

# Chemical-Mechanical Planarization of Semiconductor Materials

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# Contents

## 1 Introduction

<i>Michael R. Oliver</i> .....	1
1.1 Original Motivation for CMP .....	1
1.2 CMP Technology and Its Technical Understanding .....	1
1.3 Applications of CMP to Semiconductor Processing .....	2
1.4 Polishing Tools and Consumables of CMP Technology .....	3
1.5 Post CMP Cleaning .....	4
1.6 Integration of CMP Into the Semiconductor Fabrication Process ..	5
1.7 Pattern Dependency Issues .....	5
1.8 Other Issues .....	6
References .....	6

## 2 CMP Technology

<i>Michael R. Oliver</i> .....	7
2.1 Background and Motivation for CMP .....	7
2.2 Description of the CMP Process .....	8
2.3 Polishing Equipment .....	8
2.4 Polish Process .....	12
2.5 Planarization .....	14
2.6 Polish Process Variables .....	19
2.7 Scales and Random Polishing Effects .....	26
2.8 Random Effects .....	30
2.9 Slurries with Particles Other than Silica .....	31
2.10 Non-ILD Non-Metal CMP .....	33
2.11 Conclusion .....	37
References .....	38

## 3 Metal Polishing Processes

<i>D.R. Evans</i> .....	41
3.1 Metal Polishing Processes .....	41
3.2 Evolution of Damascene Surface Morphology During Polishing ...	46
3.3 Specifics of Tungsten and Copper Polishing .....	51
3.4 Metal Polishing Chemistry .....	60
3.5 Acid–Base Equilibria .....	62
3.6 Buffering .....	63

3.7	Oxidation–Reduction Reactions .....	66
3.8	Half Reactions .....	67
3.9	Electrode Potentials .....	67
3.10	Complexation .....	71
3.11	Surfactants and Inhibitors .....	74
3.12	The Future of Metal Polishing .....	79
	References .....	80
<b>4 Metal CMP Science</b>		
	<i>David Stein</i> .....	85
4.1	Introduction .....	85
4.2	Tungsten Experimental Data – Chemical and Electrochemical....	86
4.3	Tungsten Experimental Data – Role of Slurry Particle .....	97
4.4	Conclusions on Mechanisms on W CMP .....	103
4.5	Copper Experimental Data – Chemical and Electrochemical ....	104
4.6	Copper Summary .....	118
4.7	CMP Removal Models .....	119
4.8	Tungsten Model of Paul .....	120
4.9	Tungsten Model of Stein et al. ....	124
4.10	Copper Model of Babu et al. ....	127
4.11	Model Summary .....	129
4.12	Future Trends .....	130
	References .....	131
<b>5 Equipment Used in CMP Processes</b>		
	<i>Thomas Tucker</i> .....	133
5.1	CMP Tool Requirements .....	133
5.2	Rotary CMP Tools .....	138
5.3	Rotary Kinematics .....	139
5.4	Carousel Systems .....	142
5.5	Orbital Systems .....	143
5.6	Linear Systems .....	146
5.7	Modified Grinding Systems .....	148
5.8	Web Format Tools .....	149
5.9	Electrochemical Mechanical Planarization .....	151
5.10	Carrier Technology .....	151
5.11	Pad Conditioning .....	155
5.12	Endpointing .....	158
5.13	Summary .....	163
	References .....	163
<b>6 CMP Polishing Pads</b>		
	<i>David B. James</i> .....	167
6.1	Introduction .....	167
6.2	Polymer Requirements for Polishing Pads .....	167

6.3	Basics of Polyurethanes .....	170
6.4	Types of Commercially Available Polishing Pads and Their Manufacture .....	172
6.5	Control of Polyurethane Pad Properties .....	180
6.6	Control of Pad Properties Through Pad Geometry .....	189
6.7	Relationships Between Pad Properties and Polishing Performance	197
6.8	Slurryless Pad Technology .....	207
6.9	Future Trends in Polishing Pads .....	208
6.10	Acknowledgements .....	210
	References .....	210
<b>7 Fundamentals of CMP Slurry</b>		
	<i>Karl Robinson</i> .....	215
7.1	Introduction: Basic Components of CMP Slurries .....	215
7.2	Surface Science and Electrochemistry in CMP Slurry .....	217
7.3	Slurry as a Suspension .....	222
7.4	Solids Content .....	232
7.5	Slurry Handling .....	241
7.6	Future Trends in Slurry .....	245
7.7	Summary .....	246
	References .....	247
<b>8 CMP Cleaning</b>		
	<i>John de Larios</i> .....	251
8.1	Introduction .....	251
8.2	Polishing and the Control of CMP Defects .....	259
8.3	Mechanical Brush Scrubbing for CMP Cleaning .....	260
8.4	Non-Contact Processes for CMP Cleaning .....	263
8.5	Other Cleaning Technologies .....	264
8.6	Cleaning of Oxides, W, STI, Cu, and low k Materials .....	265
8.7	Future Directions for CMP Cleaning .....	276
8.8	Conclusion .....	277
	References .....	277
<b>9 Patterned Wafer Effects</b>		
	<i>D. Boning and D. Hetherington</i> .....	283
9.1	Introduction .....	283
9.2	Planarization Terminology and Characterization .....	283
9.3	Pattern Dependencies in Dielectric CMP .....	299
9.4	Metal CMP Pattern Dependencies .....	326
	References .....	344

**10 Integration Issues of CMP**

<i>K.M. Robinson, K. DeVriendt and D.R. Evans</i> .....	351
10.1 Oxide CMP Integration .....	351
10.2 Tungsten CMP .....	373
10.3 STI Integration .....	384
10.4 Copper Damascene Integration .....	396
10.5 Other Applications of CMP .....	407
References .....	412
<b>Appendix: Pourbaix Diagrams</b> .....	419
References .....	425